Substitute Form PTO 449 U.A. Department of Commerce (Modified)

Information Disclosure Statement by Applicant
(Use several sheets if necessary)

(37 CFR §1.98(b))

Attorney's Docket No. 12732-092002

Application No. 12732-092002

Applicant Shunpei Yamazaki et al.

Filing Date November 24, 2003

Group Art Unit 2811

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(37 CFR §1.98(b))

U.S. Department of Commerce Patent and Trademark Office Attorney's Dockerso. 12732-092002 & PRAGENTAL 10/718,584

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U.S. Department of Commerce Pagent and Trademark Office

Attorney's Docket No. 12732-092002

Application No. 10/718,584

Information Disclosure Statement
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(Use several sheets if necessary)

Applicant Shunpei Yamazaki et al.

Filing Date November 24, 2003 Group Art Unit 2811

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Attorney's Docket No. 12732-092002

Application No. 10/718,584

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Applicant

Shunpei Yamazaki et al.

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(37 CFR §1.98(b))

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